



DSS20200L

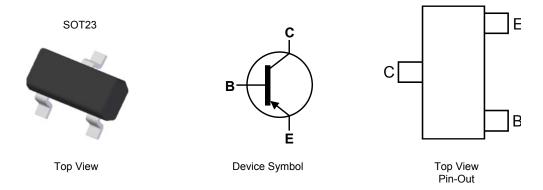
20V PNP LOW SATURATION TRANSISTOR IN SOT23

Features

- BV_{CEO} > -20V
- I_C = -2A Continuous Collector Current
- I_{CM} = -4A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -120mV @ -1A
- $R_{CE(SAT)} = 40 m\Omega$ for a low equivalent on-resistance
- Complimentary NPN Type : DSS20201L
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (approximate)



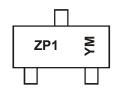
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS20200L-7	ZP1	7	8	3,000
DSS20200L-13	ZP1	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZP1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-7	V
Peak Pulse Collector Current	I _{CM}	-4	Α
Continuous Collector Current	Ic	-2	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	0	600	mW	
Power Dissipation	(Note 6)	P_{D}	1.2		
Thermal Desigtance Junction to Ambient Air	(Note 5)	0	209	°C/W	
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{ heta JA}$	104		
Thermal Resistance, Junction to Leads (Note 7		$R_{ heta JL}$	75		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

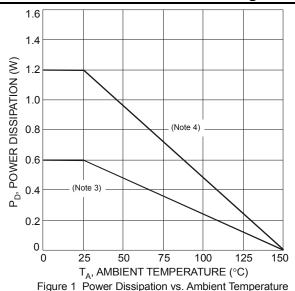
 6. Same as note (5), except mounted on 25mm x 25mm 1oz copper.

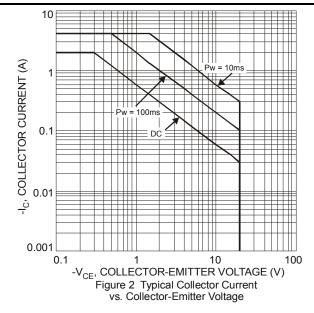
 7. Thermal resistance from junction to solder-point (at the end of collector lead).

 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating information





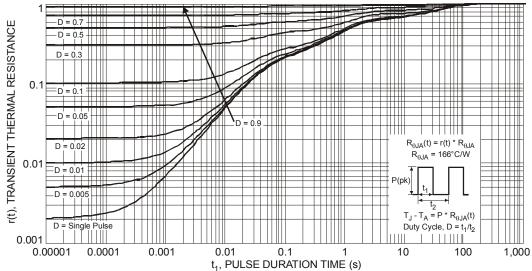


Figure 3 Transient Thermal Response

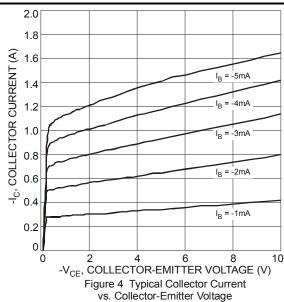


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS	•					
Collector-Base Breakdown Voltage	BV _{CBO}	-20	_	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-20	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}	_	_	-100	nA	V _{CB} = -20V, I _E = 0
Emitter-Base Cutoff Current	I _{EBO}	_	_	-100	nA	V _{EB} = -7V, I _C = 0
ON CHARACTERISTICS (Note 9)						
		250	_	_		$V_{CE} = -2V, I_{C} = -10mA$
DC Current Gain	h	250	_	_		$V_{CE} = -2V, I_{C} = -500mA$
DC Current Gain	h _{FE}	180	_	_	_	$V_{CE} = -2V, I_{C} = -1A$
		150	_	_		V _{CE} = -2V, I _C = -2A
		_	_	-13	mV	I _C = -0.1A, I _B = -10mA
Collector-Emitter Saturation Voltage	1,,	_	-50	-90		I _C = -1A, I _B = -100mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-100	-120		I _C = -1A, I _B = -10mA
		_	-80	-180		I _C = -2A, I _B = -200mA
Equivalent On-Resistance	R _{CE(SAT)}	_	40	90	mΩ	I _C = -2A, I _B = -200mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-0.9	V	I _C = -1A, I _B = -10mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}	_	_	-0.9	V	V _{CE} = -2V, I _C = -1A
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	_	_	MHz	V _{CE} = -5V, I _C = -100mA, f = 100MHz
Output Capacitance	C _{obo}	_	_	100	pF	V _{CB} = -3V, f = 1MHz
Input Capacitance	C _{ibo}	_	_	330	pF	V _{EB} = -0.5V, f = 1MHz
SWITCHING CHARACTERISTICS	•			•		
Turn-On Time	ton	_	_	180	ns	451/ 1 750 4
Delay Time	t _d	_	_	60	ns	$V_{CC} = -15V$, $I_C = -750$ mA, $I_{B1} = -15$ mA
Rise Time	t _r	_	_	120	ns	7 IB1 15 IIIA
Turn-Off Time	t _{off}	_	_	430	ns	45)(1, 750, 4
Storage Time	ts	_	_	300	ns	$V_{CC} = -15V$, $I_{C} = -750$ mA, $I_{B1} = I_{B2} = -15$ mA
Fall Time	t _f			130	ns	7181 - 182 13IIIA

Note:

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



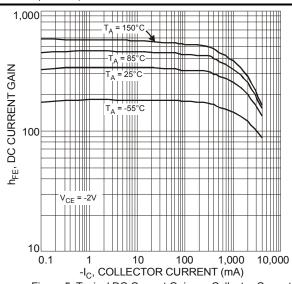


Figure 5 Typical DC Current Gain vs. Collector Current

^{9.} Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%



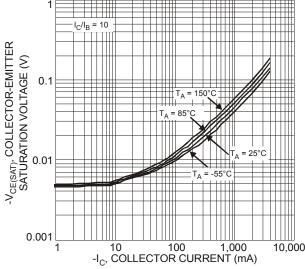


Figure 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

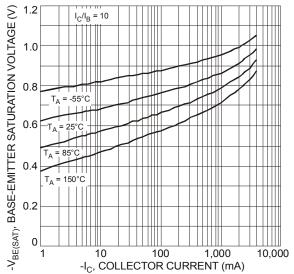


Figure 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

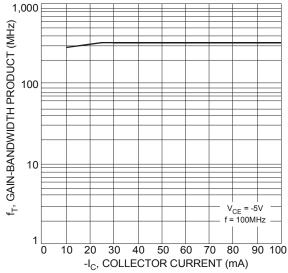


Figure 10 Typical Gain-Bandwidth Product vs. Collector Current

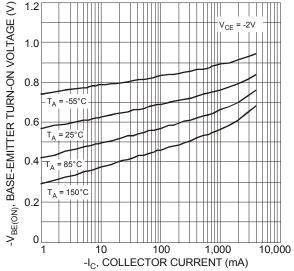
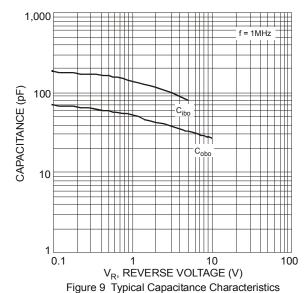


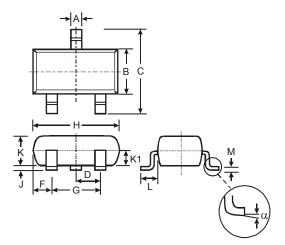
Figure 7 Typical Base-Emitter Turn-On Voltage vs. Collector Current





Package Outline Dimensions

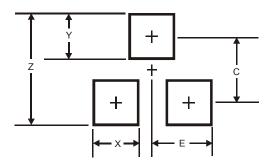
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Η	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
Е	1.35



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